

ACST4

Overvoltage protected AC switch

Features

- Triac with overvoltage protection
- Low I_{GT} (<10 mA) or high immunity (I_{GT}<35 mA) version
- High noise immunity: static dV/dt > 1000 V/µs
- TO-220FPAB insulated package: 1500 V rms

Benefits

- Enables equipment to meet IEC 61000-4-5
- High off-state reliability with planar technology
- Needs no external overvoltage protection
- Reduces the power passive component count
- High immunity against fast transients described in IEC 61000-4-4 standards

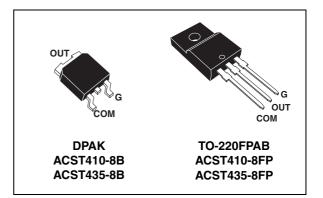
Applications

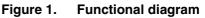
- AC mains static switching in appliance and industrial control systems
- Drive of medium power AC loads such as:
 Universal motor of washing machine drum
 - Compressor for fridge or air conditioner

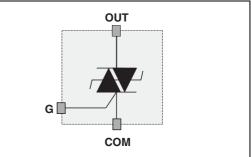
Description

The ACST4 series belongs to the ACS™/ACST power switch family built with A.S.D.[®] (application specific discrete) technology. This high performance device is suited to home appliances or industrial systems, and drives loads up to 4 A.

This ACST4 switch embeds a Triac structure and a high voltage clamping device able to absorb the inductive turn-off energy and withstand line transients such as those described in the IEC 61000-4-5 standards. The ACST410 needs only a low gate current to be activated ($I_{GT} < 10$ mA) and still shows a high noise immunity complying with IEC standards such as IEC 61000-4-4 (fast transient burst test).









Symbol	Value	Unit
I _{T(RMS)}	4	А
V _{DRM} /V _{RRM}	800	V
I _{GT} (ACST410)	10	mA
I _{GT} (ACST435)	35	mA

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1 Characteristics

Absolute ratings (limiting values)					
Paramete	Value	Unit			
	TO-220FPAB	T _c = 102 °C	4		
On-state rms current (full sine wave)	DPAK	T _c = 112 °C	4	А	
	DPAK with 0.5 cm ² copper	T _{amb} = 60 °C	1	^	
Non repetitive surge peak on-state current	F = 60 Hz	t _p = 16.7 ms	32	А	
T_j initial = 25 °C, (full cycle sine wave)	F = 50 Hz	t _p = 20 ms	30	А	
I ² t for fuse selection		t _p = 10 ms	6	A ² s	
$\label{eq:F} \begin{array}{l} \mbox{Critical rate of rise on-state current} \\ \mbox{I}_G = 2 \ x \ \mbox{I}_{GT_r} \ (t_r \leq 100 \ \mbox{ns}) \end{array} \hspace{0.5cm} F = 120 \end{array}$		T _j = 125 °C	100	A/µs	
Non repetitive line peak pulse voltage ⁽¹⁾	2	kV			
Average gate power dissipation $T_j = 125 \text{ °C}$			0.1	W	
Peak gate power dissipation ($t_p = 20 \ \mu s$) $T_j = 125 \ ^{\circ}C$		10	W		
Peak gate current (t _p = 20 μ s) T _j = 125 °C		1.6	А		
Storage temperature range			-40 to +150	°C	
Operating junction temperature range			-40 to +125	°C	
Maximum lead solder temperature during 10 ms (at 3 mm from plastic case)			260	°C	
Insulation rms voltage TO-220FPAB			1500	V	
	ParameteParameteOn-state rms current (full sine wave)Non repetitive surge peak on-state currentTj initial = 25 °C, (full cycle sine wave)I ² t for fuse selectionCritical rate of rise on-state currentIG = 2 x IGT, (tr ≤ 100 ns)Non repetitive line peak pulse voltage ⁽¹⁾ Average gate power dissipationPeak gate power dissipation (tp = 20 µs)Peak gate current (tp = 20 µs)Storage temperature rangeOperating junction temperature rangeMaximum lead solder temperature during 1	ParameterParameterTO-220FPABDPAKDPAK with 0.5 cm² copperNon repetitive surge peak on-state current T _j initial = 25 °C, (full cycle sine wave)F = 60 HzF = 60 HzF = 50 HzI²t for fuse selectionCritical rate of rise on-state current I _G = 2 x I _{GT} , (t _r ≤ 100 ns)F = 120 HzNon repetitive line peak pulse voltage ⁽¹⁾ Average gate power dissipationPeak gate power dissipationPeak gate current (t _p = 20 µs)Storage temperature rangeOperating junction temperature rangeMaximum lead solder temperature during 10 ms (at 3 mm from	ParameterParameterOn-state rms current (full sine wave)TO-220FPAB $T_c = 102 \ ^{\circ}C$ DPAK $T_c = 112 \ ^{\circ}C$ DPAK with $0.5 \ ^{\circ}cm^2 \ copper$ $T_{amb} = 60 \ ^{\circ}C$ Non repetitive surge peak on-state current T_j initial = 25 \ ^{\circ}C, (full cycle sine wave) $F = 60 \ Hz$ $t_p = 16.7 \ ms$ I ² t for fuse selection $F = 50 \ Hz$ $t_p = 20 \ ms$ I ² t for fuse selection $t_p = 10 \ ms$ Critical rate of rise on-state current $I_G = 2 \ x \ I_{GT,} \ (t_r \le 100 \ ns)$ $F = 120 \ Hz$ $T_j = 125 \ ^{\circ}C$ Non repetitive line peak pulse voltage (1) $T_j = 25 \ ^{\circ}C$ $T_j = 125 \ ^{\circ}C$ Average gate power dissipation ($t_p = 20 \ \mu$ s) $T_j = 125 \ ^{\circ}C$ Peak gate current ($t_p = 20 \ \mu$ s) $T_j = 125 \ ^{\circ}C$ Peak gate current ($t_p = 20 \ \mu$ s) $T_j = 125 \ ^{\circ}C$ Peak gate current ($t_p = 20 \ \mu$ s) $T_j = 125 \ ^{\circ}C$ Peak gate current ($t_p = 20 \ \mu$ s) $T_j = 125 \ ^{\circ}C$ Peak gate current ($t_p = 20 \ \mu$ s) $T_j = 125 \ ^{\circ}C$ Storage temperature rangeOperating junction temperature rangeOperating junction temperature rangeMaximum lead solder temperature during 10 ms (at 3 mm from plastic case)	$\begin{tabular}{ c c c c } \hline Parameter & Value \\ \hline Parameter & Value \\ \hline \hline Parameter & Value & T_c = 102 \ ^{\circ}C & 4 \\ \hline DPAK & T_c = 112 \ ^{\circ}C & 1 \\ \hline DPAK & with & T_c = 112 \ ^{\circ}C & 1 \\ \hline DPAK & with & 0.5 \ ^{\circ}C \ ^{\circ}C \ ^{\circ}C & 1 \\ \hline DPAK & with & 0.5 \ ^{\circ}C \ ^{\circ}C \ ^{\circ}C & 1 \\ \hline DPAK & with & 0.5 \ ^{\circ}C \ ^{\circ}C \ ^{\circ}C & 1 \\ \hline Parameter & T_p = 16.7 \ ^{\circ}MS & 32 \\ \hline F = 50 \ ^{\circ}Hz & t_p = 16.7 \ ^{\circ}MS & 30 \\ \hline I^2t \ for fuse selection & t_p = 10 \ ^{\circ}MS & 6 \\ \hline Critical rate of rise on-state current \\ I_G = 2 \times I_{GT,} \ (t_r \le 100 \ ^{\circ}NO \$	

Table 2.Absolute ratings (limiting values)
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1. According to test described in IEC 61000-4-5 standard and Figure 19.

Table 3. Electrical characteristics

Symbol	Test conditions	Quadrant	Тj		ACST410	ACST435	Unit
I _{GT} ⁽¹⁾	V_{OUT} = 12 V, R _L = 33 Ω	- -	25 °C	MAX.	10	35	mA
V _{GT}	V_{OUT} = 12 V, R _L = 33 Ω	- -	25 °C	MAX.	1.0	1.1	V
V _{GD}	$V_{OUT} = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$ I - II - III		125 °C	MIN.	0.2		V
I _H (2)	I _{OUT} = 500 mA		25 °C	MAX.	20	25	mA
ΙL	I _G = 1.2 x I _{GT} I - II - III		25 °C	MAX.	40	60	mA
dV/dt (2)	V _{OUT} = 67 % V _{DRM} , gate open		125 °C	MIN.	500	1000	V/µs
(dl/dt) _c ⁽²⁾	Without snubber		125 °C	MIN.		5	A/ms
$(dI/dt)_{c}^{(2)}$	(dV/dt) _c = 15 V/µs		125 °C		2		A/ms
V _{CL}	$I_{CL} = 0.1 \text{ mA}, t_p = 1 \text{ ms}$		25 °C	MIN.	85	50	V

1. Minimum I_{GT} is guaranteed at 5% of I_{GT} max

2. For both polarities of OUT pin referenced to COM pin

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Symbol	Test conditions			Value	Unit
V _{TM} ⁽¹⁾	$I_{OUT} = 5.6 \text{ A}, t_p = 500 \ \mu \text{s}$	T _j = 25 °C	MAX.	1.7	V
V _{T0} ⁽¹⁾	Threshold voltage	T _j = 125 °C	MAX.	0.9	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 125 °C	MAX.	110	mΩ
I _{DRM}		T _j = 25 °C	MAX.	20	μA
I _{RRM}	$V_{OUT} = V_{DRM} / V_{RRM}$	T _j = 125 °C	MAX.	500	μA

Table 4.Static characteristics

1. For both polarities of OUT pin referenced to COM pin

Table 5.Thermal resistances

Symbol	Parameter	Value	Unit	
Dt	Junction to ambient	TO-220FPAB	60	°C/W
Rt _{h(j-a)}	Junction to ambient (soldered on 0.5 cm ² copper pad)	DPAK	70	C/ VV
R _{th(j-c)}	lunction to eace for full quelo sino wave conduction	TO-220FPAB	4.6	°C/W
	Junction to case for full cycle sine wave conduction	DPAK	2.6	C/ VV

Figure 2. Maximum power dissipation versus Figure 3. on-state rms current

On-state rms current versus case temperature (full cycle)

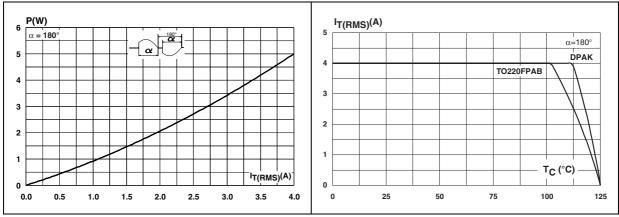
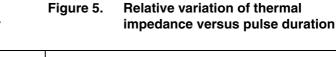




Figure 4. On-state rms current versus ambient temperature (free air convection, full cycle)



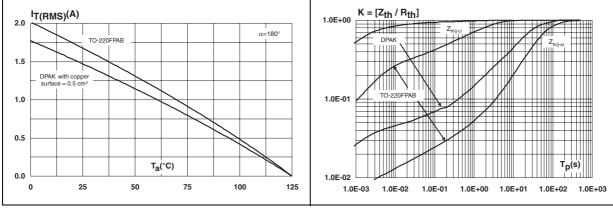
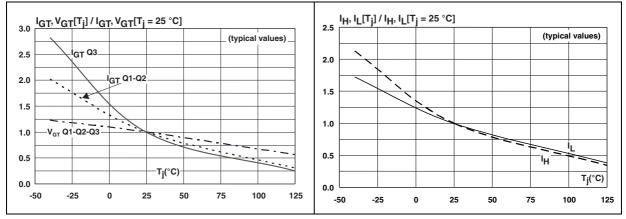


Figure 6. Relative variation of gate trigger current (I_{GT}) and voltage (V_{GT}) versus junction temperature

Figure 7. **Relative variation of holding** current (I_H) and latching current (I_L) versus junction temperature

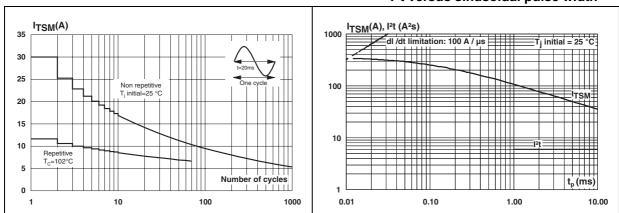


Surge peak on-state current Figure 8. versus number of cycles

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Figure 9.

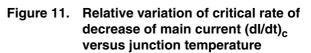
Non repetitive surge peak on-state current and corresponding value of I²t versus sinusoidal pulse width



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Figure 10. On-state characteristics (maximum values)



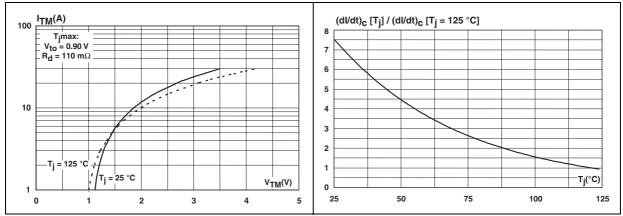
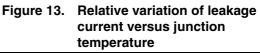


Figure 12. Relative variation of static dV/dt immunity versus junction temperature (gate open)



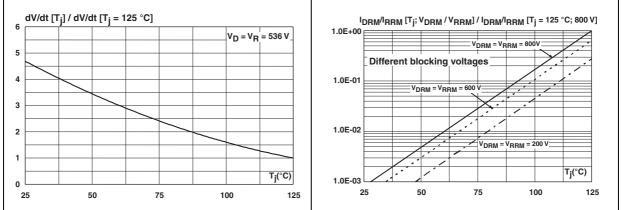
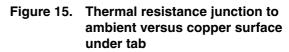
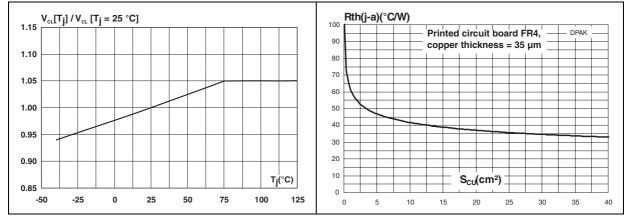


Figure 14. Relative variation of the clamping voltage (V_{CL}) versus junction temperature (minimum values)







2 Application information

2.1 Typical application description

The ACST4 device has been designed to control medium power load, such as AC motors in home appliances. Thanks to its thermal and turn off commutation performances, the ACST4 switch is able to drive an inductive load up to 4 A with no turn off additional snubber. It also provides high thermal performances in static and transient modes such as the compressor inrush current or high torque operating conditions of an AC motor. Thanks to its low gate triggering current level, the ACST4 can be driven directly by an MCU through a simple gate resistor as shown *Figure 16* and *Figure 17*.

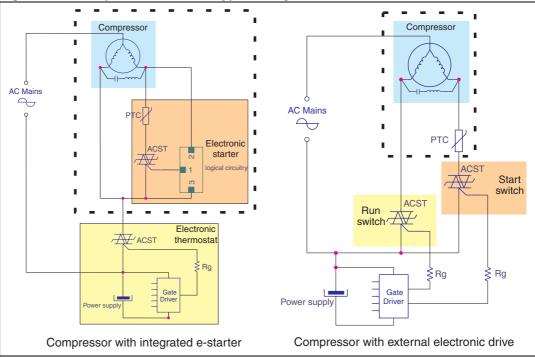


Figure 16. Compressor control – typical diagrams



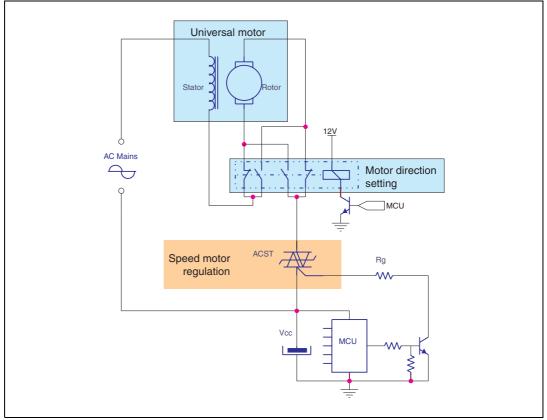


Figure 17. Universal drum motor control – typical diagram

2.2 AC line transient voltage ruggedness

In comparison with standard Triacs, which are not robust against surge voltage, the ACST4 is self-protected against over-voltage, specified by the new parameter V_{CL} . The ACST4 switch can safely withstand AC line transient voltages either by clamping the low energy spikes, such as inductive spikes at switch off, or by switching to the on state (for less than 10 ms) to dissipate higher energy shocks through the load. This safety feature works even with high turn-on current ramp up.

The test circuit of *Figure 18* represents the ACST4 application, and is used to stress the ACST switch according to the IEC 61000-4-5 standard conditions. With the additional effect of the load which is limiting the current, the ACST switch withstands the voltage spikes up to 2 kV on top of the peak line voltage. The protection is based on an overvoltage crowbar technology. The ACST4 folds back safely to the on state as shown in *Figure 19*. The ACST4 recovers its blocking voltage capability after the surge and the next zero current crossing. Such a non repetitive test can be done at least 10 times on each AC line voltage polarity.



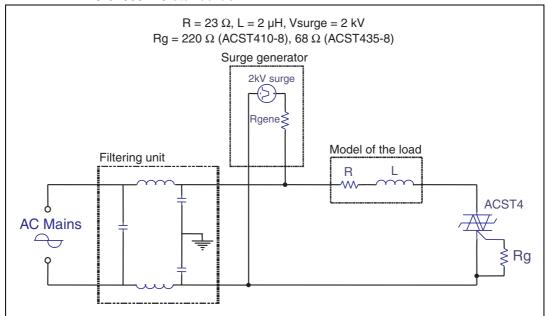
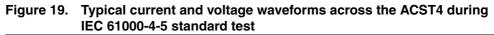
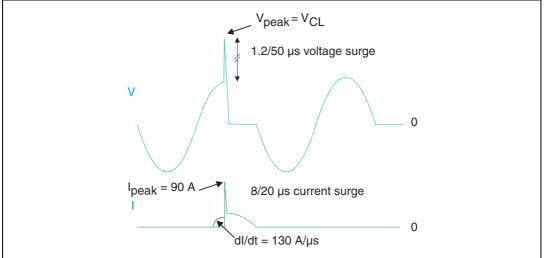


Figure 18. Overvoltage ruggedness test circuit for resistive and inductive loads for IEC 61000-4-5 standards





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3 Ordering information scheme

Figure 20. Ordering information scheme

AC switch	
Тороlоду	
T = Triac	
On-state rms current	
4 = 4 A	
Triggering gate current	
10 = 10 mA	
35 = 35 mA	
Repetitive peak off-state voltage 8 = 800V	
Package	
B = DPAK	
FP = TO-220FPAB	
Delivery mode	
TR = Tape and reel	

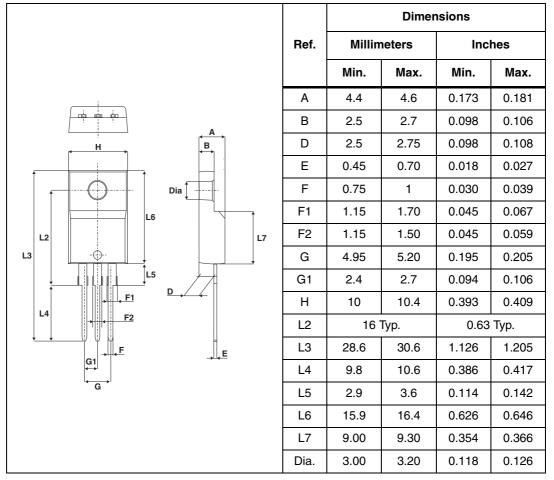


4 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value(TO220FPAB): 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK[®] is an ST trademark.

Table 6.TO-220FPAB dimensions





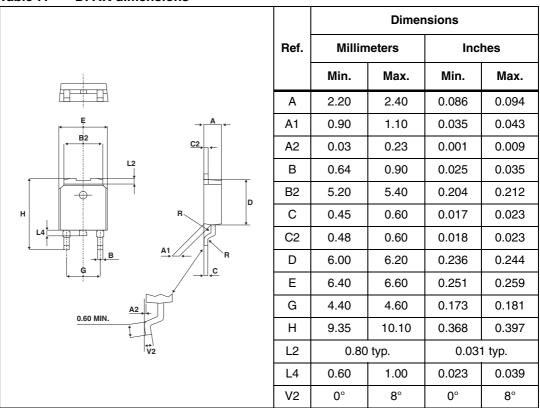
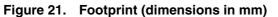
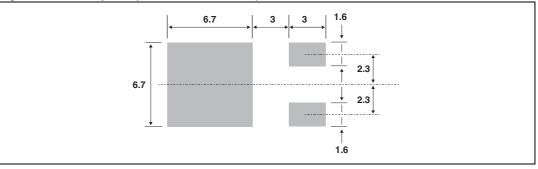


Table 7.DPAK dimensions







5 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base Qty	Delivery mode
ACST410-8B		DPAK	1.5 g	50	Tube
ACST410-8BTR	ACST4108	DPAK	1.5 g	1000	Tape and reel
ACST410-8FP		TO-220FPAB	2.4 g	50	Tube
ACST435-8B		DPAK	1.5 g	50	Tube
ACST435-8BTR	ACST4358	DPAK	1.5 g	1000	Tape and reel
ACST435-8FP		TO-220FPAB	2.4 g	50	Tube

6 Revision history

Table 9. Document revision history

Date	Revision	Changes	
Jan-2003	ЗA	Previous update.	
04-Jul-2007	4	Reformatted to current standard. Added package.	
18-Dec-2009	5	V_{DRM}/V_{RRM} updated to 800 V. Order codes updated.	

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